#### **MJE340G**

## Plastic Medium-Power NPN Silicon Transistor

This device is useful for high-voltage general purpose applications.

#### **Features**

- Suitable for Transformerless, Line-Operated Equipment
- High Power Dissipation Rating for High Reliability
- These Devices are Pb-Free and are RoHS Compliant\*
- Complementary to MJE350

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	300	Vdc
Emitter-Base Voltage	V <sub>EB</sub>	3.0	Vdc
Collector Current - Continuous	I <sub>C</sub>	500	mAdc
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	20 0.16	W mW/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL CHARACTERISTICS

Characteristic

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$\theta_{JC}$	6.25	°C/W

#### **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Symbol Min Max Unit

1

	,							
OFF CHARACTERISTICS								
Collector–Emitter Sustaining Voltage (I <sub>C</sub> = 1.0 mAdc, I <sub>B</sub> = 0)	V <sub>CEO(sus)</sub>	300	_	Vdc				
Collector Cutoff Current (V <sub>CB</sub> = 300 Vdc, I <sub>E</sub> = 0)	I <sub>CBO</sub>	-	100	μAdc				
Emitter Cutoff Current (V <sub>EB</sub> = 3.0 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	-	100	μAdc				

#### **ON CHARACTERISTICS**

DC Current Gain (I <sub>C</sub> = 50 mAdc, V <sub>CE</sub> = 10 Vdc)	h <sub>FE</sub>	30	240	-
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Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

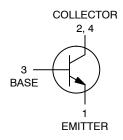


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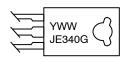
# 0.5 AMPERE POWER TRANSISTOR NPN SILICON 300 VOLTS, 20 WATTS

#### **SCHEMATIC**





#### **MARKING DIAGRAM**



Y = Year

WW = Work Week

JE340 = Device Code

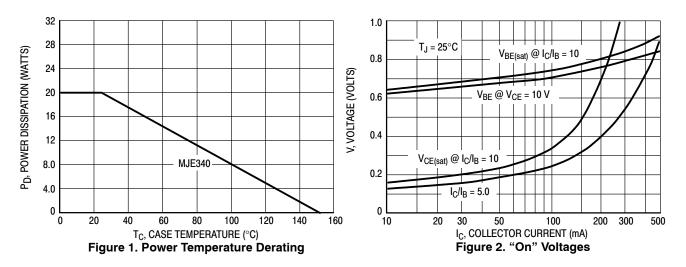
G = Pb-Free Package

#### **ORDERING INFORMATION**

Device	Package	Shipping
MJE340G	TO-225 (Pb-Free)	500 Units/Box

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### MJE340G



#### **ACTIVE-REGION SAFE OPERATING AREA**

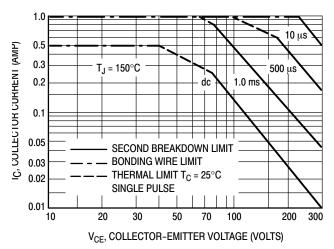
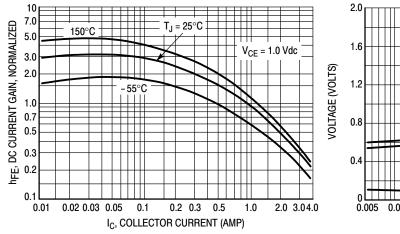


Figure 3. MJE340

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C$  –  $V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.The data of Figure 3 is based on  $T_{J(pk)}=150\,^{\circ}\mathrm{C};\ T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)}\leq150\,^{\circ}\mathrm{C}.$  At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

#### **MJE340G**



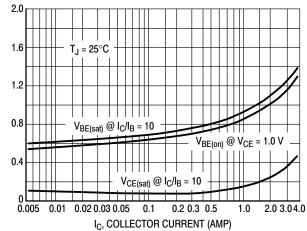


Figure 4. DC Current Gain

Figure 5. "On" Voltage

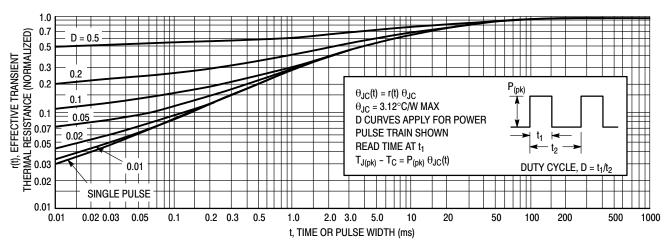


Figure 6. Thermal Response

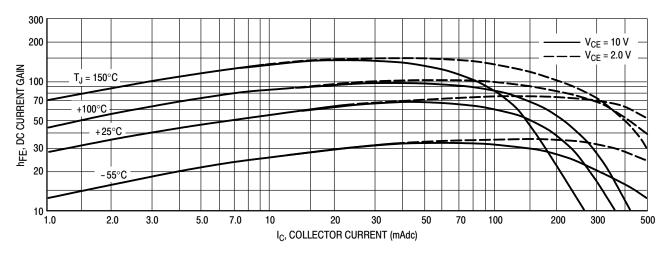
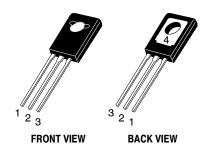


Figure 7. DC Current Gain

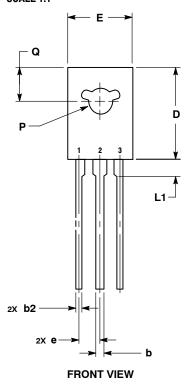
### **MECHANICAL CASE OUTLINE**

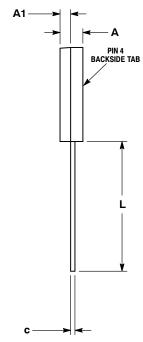


TO-225 CASE 77-09 **ISSUE AD** 

**DATE 25 MAR 2015** 

#### SCALE 1:1



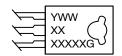


**SIDE VIEW** 

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS. 3. NUMBER AND SHAPE OF LUGS OPTIONAL.

	MILLIMETERS				
DIM	MIN	MAX			
Α	2.40	3.00			
A1	1.00	1.50			
b	0.60	0.90			
b2	0.51	0.88			
С	0.39	0.63			
D	10.60	11.10			
E	7.40	7.80			
е	2.04	2.54			
L	14.50 16.63				
L1	1.27 2.5				
P	2.90	3.30			
Q	3.80 4.20				

#### **GENERIC MARKING DIAGRAM\***



= Year ww = Work Week XXXXX = Device Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

2., 4. DRAIN 3. GATE

= Pb-Free Package

	EMITTER COLLECTOR BASE	2., 4.	CATHODE ANODE GATE	STYLE 3: PIN 1. 2., 4. 3.	COLLECTOR	,	ANODE 1 ANODE 2 GATE	STYLE 5: PIN 1. 2., 4. 3.	
STYLE 6: PIN 1.	CATHODE	STYLE 7: PIN 1.	MT 1	STYLE 8: PIN 1.	SOURCE	STYLE 9: PIN 1.	GATE	STYLE 10: PIN 1.	SOURCE

2., 4. GATE 3. DRAIN

DRAIN

2., 4. 3. DRAIN

2., 4. GATE 3. MT 2

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2., 4. 3. GATE

ANODE

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